

## Thermal Atomic Layer Etching of Ternary Indium Gallium Phosphide Based on Fluorination and Ligand-exchange Reactions

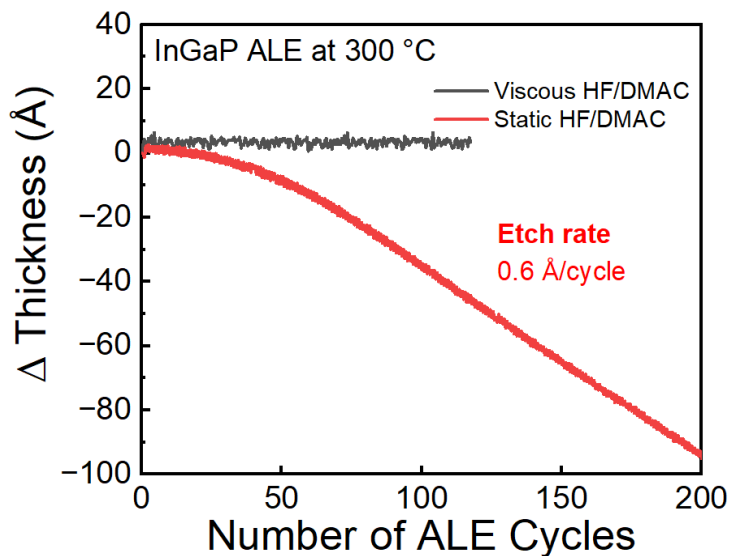


Figure 1. InGaP ALE using HF and DMAC with viscous and static exposures at 300 °C

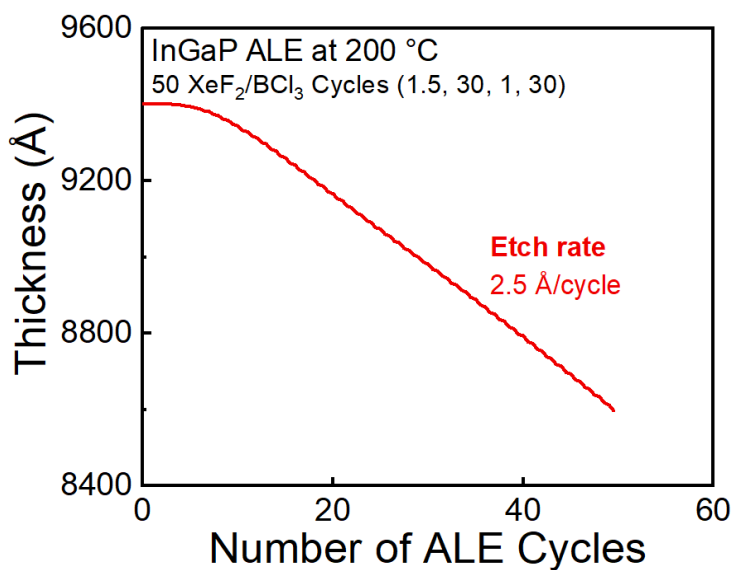


Figure 2. InGaP ALE using viscous XeF<sub>2</sub> and BCl<sub>3</sub> exposures at 200 °C